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# Rec'd PST/PTO 0 7 JUL 2005 INTERNATIONAL PRELIMINARY EXAMINATION REPORT

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AIII INT	ERNATIONAL PRELIM	UNARY EXAMIN				
	(PCT Artic	le 36 and Rule 70)	10/541583			
Applicant's or agent's file reference NE-70144WO	FOR FURTHER	ACTION See Notifi	cation of Transmittal of Interna Examination Report (Form PCT/IPEA			
International application No. PCT/JP2003/01603		International filing date (day/month/year) Priority date (day/month/year)  15 December 2003 (15.12.2003) 07 January 2003 (07.01.2003)				
International Patent Classification H01L 29/812	on (IPC) or national classification	and IPC				
Applicant	NEC COI	RPORATION				
This international preli and is transmitted to th	minary examination report has be e applicant according to Article 3	en prepared by this Inter 6.	national Preliminary Examining Autho			
2. This REPORT consists	of a total of 4 she	ets, including this cover	sheet.			
amended and ar 70.16 and Section	so accompanied by ANNEXES, i. e the basis for this report and/or son 607 of the Administrative Instructions of a total of1	heets containing rectific uctions under the PCT).	ion, claims and/or drawings which have ations made before this Authority (see			
NZ posice	dications relating to the following	; items:				
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□ Non e	stablishment of opinion with rega	rd to novelty, inventive s	step and industrial applicability			
· · ·	of unity of invention	•				
		with regard to novelty, i ch statement	inventive step or industrial applicability			
VI Certai	n documents cited					
VII Certain defects in the international application			*			
VIII Certai	n observations on the internations	d application .				
Date of submission of the den	nand	Date of completion				
15 December	2003 (15.12.2003)	06 S	eptember 2004 (06.09.2004)			
Name and mailing address of	the IPEA/JP	Authorized officer				
Facsimile No.		Telephone No.	•			

International application No.

PCT/JP2003/016033

## INTERNATIONAL PRELIMINARY EXAMINATION REPORT

I. Basis	of the re	port	
1. With	regard to	the elements of the international application:*	
	the inter	national application as originally filed	
$\overline{\boxtimes}$	the desc	ription:	
	pages	1-34	, as originally filed
	pages		, filed with the demand
	pages	, filed with the letter of	
	the clair	ns:	İ
	pages	1 10	, as originally filed
	pages	, as amended (together	
	pages .		, filed with the demand
	pages	19-20 , filed with the letter of	07 June 2004 (07.06.2004)
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	pages	<del>-</del>	, as originally filed
	pages	1-31	, filed with the demand
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in and	This rebeyond lacement this report 170.17).	the description, pages the claims, Nos the drawings, sheets/fig  port has been established as if (some of) the amendments had not been made, so the disclosure as filed, as indicated in the Supplemental Box (Rule 70.2(c)).**  sheets which have been furnished to the receiving Office in response to an invite as "originally filed" and are not annexed to this report since they do not the sheet containing such amendments must be referred to under item 1 and annexed to the step of the sheet containing such amendments must be referred to under item 1 and annexed to the step of the sheet containing such amendments must be referred to under item 1 and annexed to the step of the sheet containing such amendments must be referred to under item 1 and annexed to the step of the sheet containing such amendments must be referred to under item 1 and annexed to the step of the sheet containing such amendments must be referred to under item 1 and annexed to the step of the sheet containing such amendments must be referred to under item 1 and annexed to the step of the sheet containing such amendments must be referred to under item 1 and annexed to the step of the sheet containing such amendments must be referred to under item 1 and annexed to the step of the sheet containing such amendments must be referred to under item 1 and annexed to the step of the sheet containing such amendments must be referred to under item 1 and annexed to the step of the sheet containing such amendments must be referred to under item 1 and annexed to the step of the sheet containing such amendments must be referred to under item 1 and annexed to the step of the sheet containing such amendments must be referred to under item 1 and annexed to the sheet containing such amendments must be referred to under item 1 and annexed to the sheet containing such amendments must be referred to under item 1 and annexed to the sheet containing such amendment to the sheet containing such amendment to the sheet containing such amendment to the sheet	ation under Article 14 are referred to ot contain amendments (Rule 70.16
** An	y replacen	nent sheet containing such amendments must be referred to under item 1 and anno	exed to this report.



In Jonal application No.
PCT/JP03/16033

tement			
Novelty (N)	Claims	1-20	YE
	Claims		NC
Inventive step (IS)	Claims	4-6, 10-11, 16	YE
	Claims	1-3, 7-9, 12-15, 17-20	NO
Industrial applicability (IA)	Claims	1-20	YE
	Claims		NC

2. Citations and explanations

Document 1: JP, 2000-286428, A (NEC Corp.), 13 October, 2000 (13.10.00), paragraphs [0002] to [0019], Figs. 1-6

Document 2: JP, 11-176839, A (NEC Corp.), 2 July, 1999 (02.07.99), paragraph [0034], Fig. 4

Document 3: JP, 2002-359256, A (Fujitsu, Ltd.), 13 December, 2002 (13.12.02), full text, all drawings

Document 4: JP, 2001-189324, A (Ricoh Co., Ltd.), 10 July, 2001 (10.07.01), paragraphs [0013] to [0020]

Document 5: JP, 2002-222860, A (Sony Corp.), 9 August, 2002 (09.08.02), page 3, right column, line 34 to page 4, left column, line 5

### Claims 1-3 and 18-20

The subject matters of claims 1-3 and 18-20 do not appear to involve an inventive step in view of documents 1 and 2 cited in the ISR.

Document 1 discloses a field-effect transistor having an electric-field controlling electrode formed through an insulation film in an upper portion of a semiconductor structure of a group III nitride in an area between a gate electrode and a drain electrode, the electric-field controlling electrode being controllable independently from the gate electrode. Document 2 discloses, as a protective film for covering a field-effect transistor, a protective film made by laminating 35 nm silicon nitride films and 65 nm silicon oxide films. A person skilled in the art could have easily conceived of adopting the protective film of document 2 for the insulating film of document 1. Furthermore, a person skilled in the art could have set the electric potential of the electric-field controlling electrode as required.

#### Claims 7, 13-15, 17 and 18

The subject matters of claims 7, 13-15, 17 and 18 do not appear to involve an inventive step in view of documents 1 and 3 cited in the ISR.

Document 3 discloses a group III nitride semiconductor structure formed with an insulating film which has a channel layer composed of  $In_xGa_{1-x}N$ , an electron supply layer composed of  $A1_yGa_{1-y}N$ , a contact layer composed of undoped AlGaN, and a cap layer composed of GaN, and is, in an upper portion thereof, formed with an insulating film containing silicon and nitrogen as constituent elements. A person skilled in the art could have easily conceived of adopting the structure described in document 3 as the group III nitride semiconductor structure of document 1.

### Claims 8, 9, 12 and 18

The subject matters of claims 8, 9, 12 and 18 do not appear to involve an inventive step in view of documents 1, 4 and 5 cited in the ISR.

Document 4 discloses the technique of reducing a parasitic capacitance and improving high-frequency characteristics in a field-effect transistor by using an insulating film of which the permittivity is lower than 3.5. Document 5 describes that an insulating film containing silicon, oxygen and carbon as constituent elements is publicly known as an insulating film of which the permittivity is about 3.0. A person skilled in the art could have easily conceived of adopting the materials described in documents 4 and 5 for the insulating film of document 1.



Int. nal application No. PCT/JP03/16033

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	he subject matters	of claims 4-6,	10, 11 and 16	are neither de	scribed nor sug	gested in doc	uments 1-
	cited in the ISR.						
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